

Atty. Dkt. No. 016907-0935

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Susumu HASHIMOTO et al.  
Title: MAGNETORESISTANCE EFFECT  
ELEMENT WITH IMPROVED  
ANTIFERROMAGNETIC LAYER  
Appl. No.: 09/785,458  
Filing Date: 02/20/2001  
Examiner: B. Miller  
Art Unit: 2652

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**PRELIMINARY AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

This communication is further to the Response of October 2, 2002, and responsive to the Advisory Action dated October 17, 2002, concerning the above-referenced patent application.

Applicant has enclosed with this amendment a Petition for Extension of Time to make this response timely.

Please amend the application as follows:

In the Claims:

Please amend the claims as follows:

43. A magnetoresistance effect element comprising:

a spin valve film comprising a first ferromagnetic layer, a nonmagnetic layer, a second ferromagnetic layer, and an antiferromagnetic layer, wherein the nonmagnetic layer is provided between the first and second ferromagnetic layers, and the antiferromagnetic layer is provided adjacent to the first ferromagnetic layer;